





TEXAS INSTRUMENTS

CDCDB803 SNAS820A – AUGUST 2021 – REVISED MAY 2022

CDCDB803 DB800ZL-Compliant 8-Output Clock Buffer for PCIe Gen 1 to Gen 6

1 Features

- 8 LP-HCSL outputs with programmable integrated 85-Ω (default) or 100-Ω differential output terminations
- 8 hardware output enable (OE#) controls
- Additive phase jitter after PCIE Gen 6 filter: 20 fs, RMS (maximum)
- Additive phase jitter after PCIE Gen 5 filter: 25 fs, RMS (maximum)
- Additive phase jitter after DB2000Q filter: 38 fs, RMS (maximum)
- Supports Common Clock (CC) and Individual Reference (IR) architectures
 - Spread spectrum-compatible
- Output-to-output skew: < 50 ps
- Input-to-output delay: < 3 ns
- Fail-safe input
- Programmable output slew rate control
- 9 selectable SMBus addresses
- 3.3-V core and IO supply voltages
- Hardware-controlled low power mode (PD#)
- Current consumption: 72 mA maximum
- 6-mm × 6-mm, 48-pin VQFN package

2 Applications

- Microserver & tower server
- Storage area network & host bus adapter card
- Network attached storage
- Hardware accelerator
- Rack server

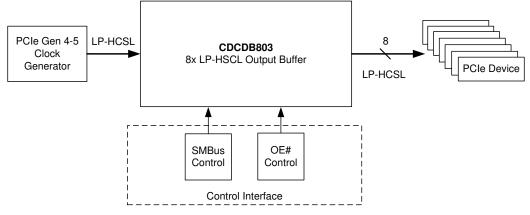
3 Description

The CDCDB803 is a 8-output LP-HCSL, DB800ZLcompliant, clock buffer capable of distributing the reference clock for PCIe Gen 1-6, QuickPath Interconnect (QPI), UPI, SAS, and SATA interfaces. The SMBus interface and eight output enable pins allow the configuration and control of all eight outputs individually. The CDCDB803 is a DB800ZL derivative buffer and meets or exceeds the system parameters in the DB800ZL specification. It also meets or exceeds the parameters in the DB2000Q specification. The CDCDB803 is packaged in a 6-mm × 6-mm, 48-pin VQFN package.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)		
CDCDB803	VQFN (48)	6.00 mm × 6.00 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.



CDCDB803 System Diagram



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision * (August 2021) to Revision A (May 2022)	Page
•	Changed the data sheet title	1
•	Added PCIe Gen 6 to the data sheet	1
•	Changed the pin descriptions for pins 5, 8 and 46	3



5 Pin Configuration and Functions

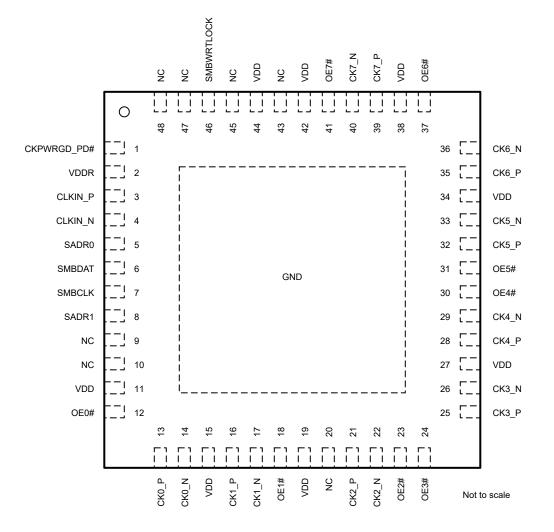


Figure 5-1. CDCDB803 RSL Package 48-Pin VQFN Top View

Table 5-1. Pin Functions

PIN NAME NO.		TYPE ⁽²⁾	DESCRIPTION
			DESCRIPTION
INPUT CLOCK		I	
CLKIN_P	3		LP-HCSL differential clock input. Typically connected directly to the differential
CLKIN_N	4	I	output of clock source.
OUTPUT CLOCKS		l	
CK0_P	13	0	LP-HCSL differential clock output of channel 0. Typically connected directly to PCIe
CK0_N	14	0	differential clock input. If unused, the pins can be left no connect.
CK1_P	16	0	LP-HCSL differential clock output of channel 1. Typically connected directly to PCIe
CK1_N	17	0	differential clock input. If unused, the pins can be left no connect.



Table 5-1. Pin Functions (continued)

PI	N	TYPE ⁽²⁾	DESCRIPTION
NAME	NO.		DESCRIPTION
CK2_P	21	0	LP-HCSL differential clock output of channel 2. Typically connected directly to PCIe
CK2_N	22	0	differential clock input. If unused, the pins can be left no connect.
CK3_P	25	0	LP-HCSL differential clock output of channel 3. Typically connected directly to PCIe
CK3_N	26	0	differential clock input. If unused, the pins can be left no connect.
CK4_P	28	0	LP-HCSL differential clock output of channel 4. Typically connected directly to PCIe
CK4_N	29	0	differential clock input. If unused, the pins can be left no connect.
CK5_P	32	0	LP-HCSL differential clock output of channel 5. Typically connected directly to PCIe
CK5_N	33	0	differential clock input. If unused, the pins can be left no connect.
CK6_P	35	0	LP-HCSL differential clock output of channel 6. Typically connected directly to PCIe
CK6_N	36	0	differential clock input. If unused, the pins can be left no connect.
CK7_P	39	0	LP-HCSL differential clock output of channel 7. Typically connected directly to PCIe
CK7_N	40	0	differential clock input. If unused, the pins can be left no connect.
MANAGEMENT ANI	D CONTROL ⁽¹⁾	I	
CKPWRGD_PD#	1	I, S, PD	Clock Power Good and Power Down multi-function input pin with internal 180 -k Ω pulldown. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. After PWRGD has been asserted high for the first time, the pin becomes a PD# pin and it controls power-down mode: LOW: Power-down mode, all output channels tri-stated. HIGH: Normal operation mode.
OE0#	12	I, S, PD	Output Enable for channel 0 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 0. HIGH: disable output channel 0.
OE1#	18	I, S, PD	Output Enable for channel 1 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 1. HIGH: disable output channel 1.
OE2#	23	I, S, PD	Output Enable for channel 2 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 2. HIGH: disable output channel 2.
OE3#	24	I, S, PD	Output Enable for channel 3, with internal 180-k Ω pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 3. HIGH: disable output channel 3.
OE4#	30	I, S, PD	Output Enable for channel 4, with internal 180-k Ω pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 4. HIGH: disable output channel 4.
OE5#	31	I, S, PD	Output Enable for channel 5, with internal 180-k Ω pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 5. HIGH: disable output channel 5.
OE6#	37	I, S, PD	Output Enable for channel 6 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 6. HIGH: disable output channel 6.
OE7#	41	I, S, PD	Output Enable for channel 7 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 7. HIGH: disable output channel 7.



Table 5-1. Pin Functions (continued)

PIN		TYPE ⁽²⁾	DESCRIPTION		
NAME	NO.		DESCRIPTION		
SADR0	5	I, S, PU / PD	SMBus address strap bit[0]. This is a 3-level input that is decoded in conjunction with pin 8 to set SMBus address. It has internal $180 \cdot k\Omega$ pullup / pulldown network biasing to GND when no connect. For a high-level input configuration, the pin should be pulled up to 3.3-V VDD through an external pullup resistor from 1k to 5k with 5% tolerance. For a low-level input configuration input, the pin should be pulled down to ground through an external pulldown resistor from 1k to 5k with 5% tolerance. For a mid-level input configuration, the pin should be left floating and not connected to VDD or ground.		
SMBDAT	6	I/O	Data pin of SMBus interface. Typically pulled up to 3.3-V VDD using external pullup resistor. The recommended pullup resistor value is > 8.5k.		
SMBCLK	7	I	Clock pin of SMBus interface. Typically pulled up to 3.3-V VDD using external pullup resistor. The recommended pullup resistor value is > 8.5k.		
SADR1	8	I, S, PU / PD	SMBus address strap bit[1]. This is a 3-level input that is decoded in conjunction with pin B4 to set SMBus address. It has internal 180-k Ω pullup / pulldown network biasing to GND when no connect. For a high-level input configuration, the pin should be pulled up to 3.3-V VDD through an external pullup resistor from 1k to 5k with 5% tolerance. For a low-level input configuration, the pin should be pulled down to ground through an external pulldown resistor from 1k to 5k with 5% tolerance. For a mid-level input configuration, the pin should be pulled down to ground through an external pulldown resistor from 1k to 5k with 5% tolerance. For a mid-level input configuration, the pin should be left floating and not connected to VDD or ground.		
SMBWRTLOCK	46	I, PD	SMBWRTLOCK: Disables write commands on SMBus. All writes will be ignored when SMBWRTLOCK is asserted (reads are not affected). Internal 180-k Ω pulldown, active high. 0 = SMBus write enabled. 1 = SMBus write disabled.		
SUPPLY VOLTAGE	AND GROUND				
VDDR	2	Р	Power supply input for input clock receiver. Connect to 3.3-V power supply rail with decoupling capacitor to GND. Place a $0.1-\mu$ F capacitor close to each supply pin between power supply and ground.		
VDD	11, 15, 19, 27, 34, 38, 42, 44	Р	3.3-V power supply for output channels and core voltage.		
GND	DAP	G	Ground. Connect ground pad to system ground.		
NO CONNECT			·		
NC	9, 10, 20, 43, 45	_	Do not connect to GND or VDD.		
NC	47, 48	_	No connect. Pins may be connected to GND, VDD, or otherwise tied to any potential within the Supply Voltage range stated in the Absolute Maximum Ratings.		

(1) The "#" symbol at the end of a pin name indicates that the active state occurs when the signal is at a low voltage level. When "#" is not present, the signal is active high. (2)

The definitions below define the I/O type for each pin.

- I = Input
- O = Output
- I / O = Input / Output
- PU / PD = Internal 180-kΩ Pullup / Pulldown network biasing to VDD/2
- PD = Internal 180-kΩ Pulldown
- S = Hardware Configuration Pin
- P = Power Supply
- G = Ground •

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{DD} , V _{DD_R}	Power supply voltage	-0.3	3.6	V
V _{IN}	IO input voltage	-0.3	3.6	V
TJ	Junction temperature		125	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±3500	M	
V _(ESD)	Lieurostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	IO, Core supply voltage	3	3.3	3.6	V
V _{DD_R}	Input supply voltage	3	3.3	3.6	V
T _A	Ambient temperature	-40		105	°C

6.4 Thermal Information

	Device Package		
THERMAL METRIC ⁽¹⁾	RSL (QFN)	UNIT	
	48 PINS		
Junction-to-ambient thermal resistance	32.2	°C/W	
Junction-to-case (top) thermal resistance	22.3	°C/W	
Junction-to-board thermal resistance	14.3	°C/W	
Junction-to-top characterization parameter	0.5	°C/W	
Junction-to-board characterization parameter	14.2	°C/W	
Junction-to-case (bottom) thermal resistance	6.1	°C/W	
	Junction-to-ambient thermal resistance Junction-to-case (top) thermal resistance Junction-to-board thermal resistance Junction-to-top characterization parameter Junction-to-board characterization parameter	THERMAL METRIC ⁽¹⁾ RSL (QFN) 48 PINS Junction-to-ambient thermal resistance 32.2 Junction-to-case (top) thermal resistance 22.3 Junction-to-board thermal resistance 14.3 Junction-to-top characterization parameter 0.5 Junction-to-board characterization parameter 14.2	

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

VDD, VDD_R = $3.3 \text{ V} \pm 5 \%$, $-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 105^{\circ}\text{C}$. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT	CONSUMPTION					
	Care supply surrent	Active mode. CKPWRGD_PD# = 1			9	mA
DD_R	Core supply current	Power-down mode. CKPWRGD_PD# = 0			2.2	
		All outputs disabled			18	
I _{DD}	IO supply current	All outputs active, 100MHz (Per output)			7.8	mA
		Power-down mode. CKPWRGD_PD# = 0			1.5	
CLOCK INI	PUT					
f _{IN}	Input frequency		50	100	250	MHz
V _{IN}	Input voltage swing	Differential voltage between CLKIN_P and CLKIN_N ⁽¹⁾	200		2300	mV _{Diff-} _{peak}
dV/dt	Input voltage edge rate	20% - 80% of input swing	0.7			V/ns
DV _{CROSS}	Total variation of V _{CROSS}	Total variation across V _{CROSS}		140		mV
DCIN	Input duty cycle		40		60	%
C _{IN}	Input capacitance ⁽²⁾	Differential capacitance between CLKIN_P and CLKIN_N pins		2.2		pF
CLOCK OL	JTPUT					
f _{ouт}	Output frequency		50	100	250	MHz
C _{OUT}	Output capacitance ⁽¹⁾	Differential capacitance between CKx_P and CKx_N pins		4		pF
V _{OH}	Output high voltage		225		270	
V _{OL}	Output low voltage	- Single-ended ^{(2) (3)}	10		150	
V _{HIGH}	Output high voltage	Measured into an AC load as defined in DB800ZL	660		850	
V _{LOW}	Output low voltage	Measured into an AC load as defined in DB800ZL	-150		150	
V _{MAX}	Output Max voltage	Measured into an AC load as defined in DB800ZL			1150	
V _{CROSS}	Crossing point voltage	(3) (4)	130		200	mV
V _{CROSSAC}	Crossing point voltage (AC load)	Measured into an AC load as defined in DB800ZL	250		550	
DV _{CROSS}	Total variation of V _{CROSS}	Variation of V _{CROSS} ⁽³⁾ ⁽⁴⁾		35	140	
V _{ovs}	Overshoot voltage	(3)			V _{OH} +75	
V _{ovs(AC)}	Overshoot voltage (AC load)	Measured into an AC load as defined in DB800ZL		V	_{ніGH} +30 0	
V _{uds}	Undershoot voltage	(3)			V _{OL} –75	
V _{uds(AC)}	Undershoot voltage	Measured into an AC load as defined in DB800ZL			V _{LOW} - 300	mV
V _{rb}	Ringback Voltage	Measured into an AC load as defined in DB800ZL and taken from Single Ended waveform (relative to V _{HIGH} and V _{LOW})	-0.2		0.2	V
Z _{DIFF}	Differential impedance (Default setting, 85 Ω)	Measured at V _{OL} /V _{OH}	81	85	89	
	Differential impedance (Output impedance selection bit =1, 100 Ω)	Measured at V _{OL} /V _{OH}	95	100	105	~
Z _{DIFF_CROS}	Differential impedance (Default setting, 85 Ω)	Measured at V _{CROSS}	68	85	102	Ω
s	Differential impedance (Output impedance selection bit = 1, 100 Ω)	Measured at V _{CROSS}	80	100	120	



VDD, VDD_R = $3.3 \text{ V} \pm 5 \%$, $-40^{\circ}\text{C} \le T_A \le 105^{\circ}\text{C}$. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITION	S	MIN	TYP	MAX	UNIT
t _{EDGE}	Differential edge rate	Measured (+-150 mV) around V	CROSS (7)	2		4	V/ns
Dt _{EDGE}	Edge rate matching	Measured (+-75 mV) V _{CROSS} (7	.)			20	%
t _{STABLE}	Power good assertion to stable clock output	CKPWRGD_PD# pin transitions from 0 to 1, f _{IN} = 100 MHz	Measured when positive output reaches 0.2V			1.8	ms
t _{DRIVE_PD#}	Power good assertion to outputs driven high	CKPWRGD_PD# pin transitions from 0 to 1, f _{IN} = 100 MHz	Measured when positive output reaches 0.2V			300	μs
t _{OE}	Output enable assertion to stable clock output	OEx# pin transitions from 1 to ()			10	
t _{OD}	Output enable de-assertion to no clock output	OEx# pin transitions from 0 to 1 CKPWRGD_PD# pin transitions from 1 to 0				10	CLKIN Periods
t _{PD}	Power-down assertion to no clock output					3	
t _{DCD}	Duty cycle distortion	Differential; f _{IN} = 100MHz, f _{IN_D}	_C = 50%	-1		1	%
t _{DLY}	Propagation delay	(5)		0.5		3	ns
t _{SKEW}	Skew between outputs	(6)				50	ps
t _{DELAY(IN-} OUT)	Input to output delay variation	Input-to-output delay variation at 100 MHz across voltage and temperature		-250		250	ps
J _{CKx_DB2000} Q ⁽⁷⁾	Additive jitter for DB2000Q	DB2000Q filter, for input of 200 differential swing @ 1.5 V/ns			0.038	ps, RMS	
	Additive jitter for PCIe6.0	PLL BW: 0.5 - 1 MHz; CDR = 10 MHz Input clock slew rate = 2 V/ns				0.02	
	Additive jitter for PCIe5.0	PCIe5.0 filter				0.025	
J _{CKx} PCIE (7)	Additive jitter for PCIe4.0	PLL BW = 2 - 5 MHz; CDR =	Input clock slew rate ≥ 1.8 V/ns			0.06	ps, RMS
	Additive jitter for PCIe3.0	10 MHz	Input clock slew rate ≥ 0.6 V/ns			0.1	
J _{CKx}	Additive jitter	f_{IN} = 100 MHz; slew rate ≥ 3 V/ 20 MHz integration bandwidth.	ns; 12 kHz to		100	160	fs, RMS
NF	Noise floor	f _{IN} = 100 MHz; f _{Offset} ≥ 10 MHz	Input clock slew rate ≥ 3 V/ns		-160	-155	dBc/Hz
SMBUS INT	ERFACE, OEx#, CKPWRGD_PD#	1					
V _{IH}	High level input voltage			2.0			V
V _{IL}	Low level input voltage					0.8	v
I _{IH}	Input leakage current	With internal pull-up/pull-down		-30		30	μA
I _{IL}	Input leakage current	With internal pull-up/pull-down		-30		30	μA
I _{IH}	Input leakage current	Without internal pull-up/pull- down	$\begin{array}{l} GND \leq V_{IN} \\ \leq V_{DD} \end{array}$	-5		5	μA
IIL	Input leakage current	Without internal pull-up/pull- down	$GND \le V_{IN} \\ \le V_{DD}$	-5		5	μA



VDD, VDD_R = $3.3 \text{ V} \pm 5 \%$, $-40^{\circ}\text{C} \le T_A \le 105^{\circ}\text{C}$. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
C _{IN}	Input capacitance				4.5		pF
C _{OUT}	Output capacitance				4.5		pF
3-LEVEL	DIGITAL INTERFACE (SADR0, SADR1)						
V _{IH}	High level input voltage			2.3			
V _{IM}	Mid level input voltage			1.25	V _{DD} /2	1.725	V
V _{IL}	Low level input voltage					0.85	
I _{IH}	Input leakage current	With internal pull-up/pull-down	$V_{IN} = V_{DD}$	-30		30	μA
I _{IL}	Input leakage current	With internal pull-up/pull-down	V _{IN} = GND	-30		30	μA
C _{IN}	Input capacitance ⁽¹⁾				4.5		pF

(1) Voltage swing includes overshoot.

(2) Not tested in production. Ensured by design and characterization.

(3) Measured into DC test load.

(4) V_{CROSS} is single-ended voltage when CKx_P = CKx_N with respect to system ground. Only valid on rising edge of CKx, when CKx_P is rising.

(5) Measured from rising edge of CLK_IN to any CKx output.

(6) Measured from rising edge of any CKx output to any other CKx output.

(7) Measured into AC test load.

6.6 Timing Requirements

VDD, VDD_R = $3.3 \text{ V} \pm 5 \%$, $-40^{\circ}\text{C} \le T_A \le 105^{\circ}\text{C}$. Typical values are at VDD = VDD_A = 3.3 V, 25°C (unless otherwise noted)

			MIN	NOM	MAX	UNIT
SMBUS-0	COMPATIBLE INTERFACE TIMING					
f _{SMB}	SMBus operating frequency		10		400	kHz
t _{BUF}	Bus free time between STOP and START		4.7			
t _{HD_STA}	START condition hold time	SMBCLK low after SMBDAT low	4			
t _{SU_STA}	START condition setup time	SMBCLK high before SMBDAT low	4.7			μs
t _{su_sто}	STOP condition setup time		4			
t _{HD_DAT}	SMBDAT hold time		300			20
t _{SU_DAT}	SMBDAT setup time		250			ns
t _{TIMEOUT}	Detect SMBCLK low timeout	In terms of device input clock frequency	1e6			cycles
t _{LOW}	SMBCLK low period		4.7			
t _{HIGH}	SMBCLK high period		4		50	μs
t _F	SMBCLK/SMBDAT fall time ⁽¹⁾				300	20
t _R	SMBCLK/SMBDAT rise time ⁽²⁾				1000	ns

(1) TF = (VIHMIN + 0.15) to (VILMAX - 0.15)

(2) TR = (VILMAX - 0.15) to (VIHMIN + 0.15)



6.7 Typical Characteristics

Figure 6-1 shows both the phase noise of the source as well as the output of the DUT (CDCDB803). It can be seen from the phase noise plot that the DUT has a very low phase noise profile with total jitter of 71 fs, rms. If we rms subtract the clock reference noise, the additive jitter of CDCDB803 under typical conditions would be lower than 71 fs, rms.

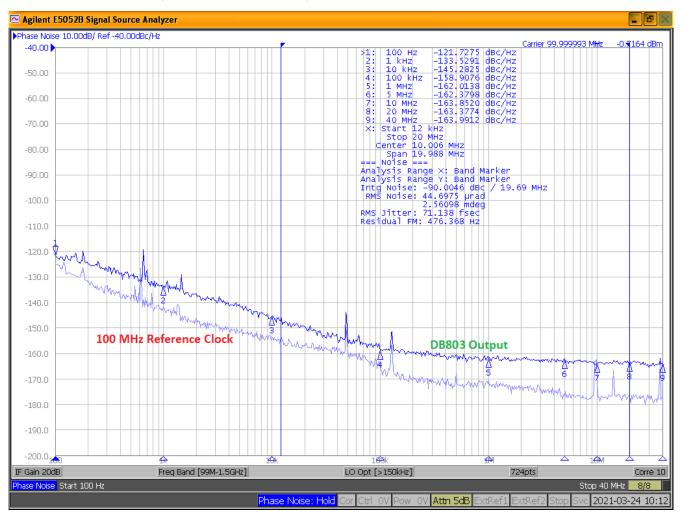


Figure 6-1. CDCDB803 Clock Out (CK0:8) Phase Noise



7 Parameter Measurement Information

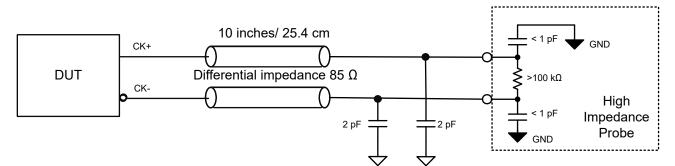
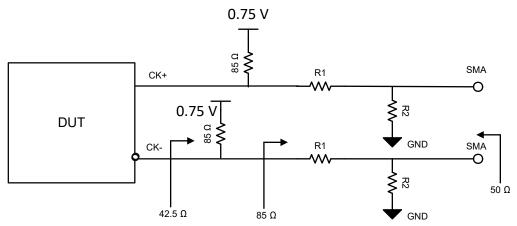


Figure 7-1. AC Test Load (Referencing Intel DB2000QL Document)



R1 = 47 Ω and R2 = 147 $\Omega.$

Figure 7-2. DC Simulation Load (Referencing Intel DB2000QL Document)

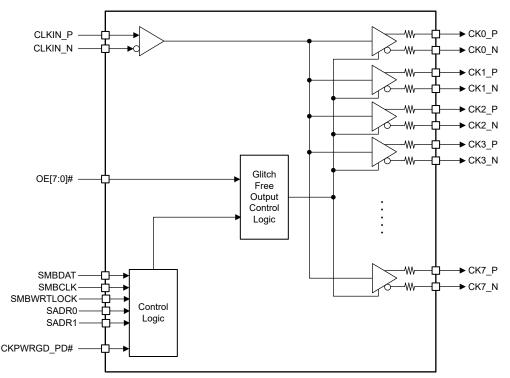


8 Detailed Description

8.1 Overview

The CDCDB803 is a low additive-jitter, low propagation delay clock buffer designed to meet the strict performance requirements for PCIe Gen 1-6, QPI, UPI, SAS, and SATA reference clocks. The CDCDB803 allows buffering and replication of a single clock source to up to eight individual outputs in the LP-HCSL format. The CDCDB803 also includes status and control registers accessible by an SMBus version 2.0 compliant interface. The device integrates a large amount of external passive components to reduce overall system cost.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Fail-Safe Input

The CDCDB803 is designed to support fail-safe input operation feature. This feature allows the user to drive the device inputs before V_{DD} is applied without damaging the device. Refer to the *Absolute Maximum Ratings* table for more information on the maximum input supported by the device.

8.3.2 Output Enable Control

The CDCDB803 uses SMBus and OE# to control the state of the output channels. The OE# pins control the state of the output with the same number. For example, the OE5# pin controls the state of the CK5 output driver. The SMBus registers may enable or disable the output when the corresponding OE# pin is held low.

8.3.3 SMBus

The CDCDB803 has an SMBus interface that is active only when CKPWRGD_PD# = 1. The SMBus allows individual enable/disable of each output.

When CKPWRGD_PD# = 0, the SMBus pins are placed in a Hi-Z state, but all register settings are retained. The SMBus register values are only retained while V_{DD} remains inside of the recommended operating voltage.

8.3.3.1 SMBus Address Assignment

The SMBus address is assigned by configuration of two pins (SADR1 and SADR0) that each support three levels. This configuration allows the CDCDB803 to assume nine different SMBus addresses.



The SMBus address pins are sampled when PWRGD is set to 1. See Table 8-1 for address pin configuration. The address can only be changed by power cycling the device.

SADR1	SADR0	SMBus ADDRESS : WRITE OPERATION (READ/WRITE=0)	SMBus ADDRESS : READ OPERATION (READ/WRITE=1)
L	L	0xD8	0xD9
L	Μ	0xDA	0xDB
L	Н	0xDE	0xDF
Μ	L	0xC2	0xC3
Μ	Μ	0xC4	0xC5
Μ	н	0xC6	0xC7
Н	L	0xCA	0xCB
Н	Μ	0xCC	0xCD
Н	Н	0xCE	0xCF

Table 8-1. SMBus Address Assignment

8.4 Device Functional Modes

8.4.1 CKPWRGD_PD# Function

The CKPWRGD_PD# pin is used to set two state variables inside of the device: PWRGD and PD#. The PWRGD and PD# variables control which functions of the device are active at any time, as well as the state of the input and output pins.

The PWRGD and PD# states are multiplexed on the CKPWRGD_PD# pin. CKPWRGD_PD# must remain below V_{OL} and not exceed V_{DDR} + 0.3 V until V_{DD} and V_{DDR} are present and within the recommended operating conditions. After CKPWRGD_PD# is set high, a valid CLKIN must be present to use PD#.

The first rising edge of the CKPWRGD_PD# pin sets PWRGD = 1. After PWRGD is set to 1, the CKPWRGD_PD# pin is used to assert PD# mode only. PWRGD variable will only be cleared to 0 with the removal of V_{DD} and V_{DDR} .

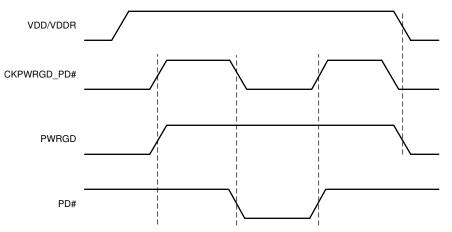


Figure 8-1. PWRGD and PD# State Changes



8.4.2 OE[7:0]# and SMBus Output Enables

Each output channel, 0 to 7, can be individually enabled or disabled by a SMBus control register bit, called SMB enable bits. Additionally, each output channel has a dedicated, corresponding, OE[7:0]# hardware pin. The OE[7:0]# pins are asynchronously asserted-low signals that may enable or disable the output.

Refer to Table 8-2 for enabling and disabling outputs through the hardware and software. Note that both the SMB enable bit must be a 1 and the OEx# pin must be an input low voltage 0 for the output channel to be active.

Control Inputs Power State Variable (Internal)			CLKIN	OE[7:0]# HARDWARE PINS AND SMBus CONTROL REGISTER BITS			CK[7:0]_P/		
CKPWRGD_P D#	PWRGD	PD#		OE[7:0]#	OUT_EN_CLK[7:0]	DRIVE_OP_ST ATE_CTRL	CK[7:0]_N		
0	0	0	Х	Х	X	Х	LOW/LOW		
	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				×	0	0	LOW/LOW	
			X(1)	1	Ŭ	1	TRI-STATE		
1		1			x	0	LOW/LOW		
		1	1			~	1	TRI-STATE	
					Runnir	Running ⁽¹⁾	0	1	Х
0		Y		0	LOW/LOW				
0		U X ⁽²⁾	X	Х	1	TRI-STATE			

Table 8-2	OF[7:0]#	# Functionality

(1) To enter the power-down state, CLKIN must remain active for at least 3 clock cycles after CKPWRGD_PD# transitions from 1 to 0.

(2) To enter the powered-up state with active clock outputs, CLKIN must be active before CKPWRGD_PD# transitions from 0 to 1.

8.4.3 Output Slew Rate Control

The CDCDB803 provides output slew rate control feature which customer can use to compensate for increased output trace length based on their board design. The slew rate of a bank of 4 outputs 0 to 3 and 4 to 7, can be changed within a given range by a SMBus control register called CAPTRIM. Refer to Table 8-16 for more information.

8.4.4 Output Impedance Control

The integrated termination on the CDCDB803 can be programmed either for 85 Ω or 100 Ω . This flexibility ensures that the customer can use the same device across various applications irrespective of the characteristic board impedance which is typically either 85 Ω or 100 Ω . This termination resistor can be changed for all the outputs as whole using bit 5 of a register called OUTSET. Refer to Table 8-14 for more information.

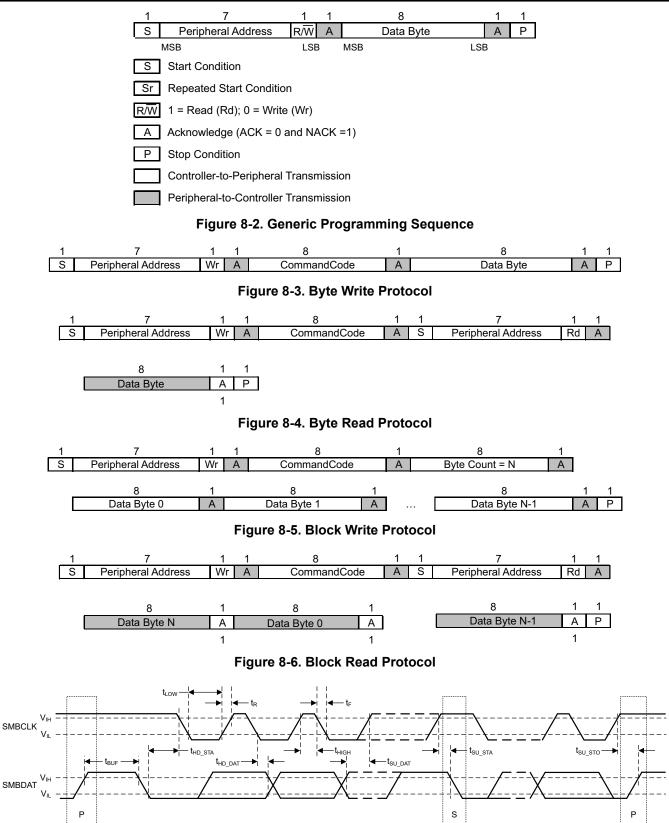
8.5 Programming

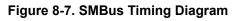
The CDCDB803 uses SMBus to program the states of its eight output drivers. See *SMBus* for more information on the SMBus programming, and *Register Maps* for information on the registers.

Table 8-3. Command Code Definition

BIT	DESCRIPTION	
7	0 = <i>Block Read</i> or <i>Block Write</i> operation 1 = <i>Byte Read</i> or <i>Byte Write</i> operation	
(6:0)	Register address for Byte operations, or starting register address for Block, operations	









8.6 Register Maps

8.6.1 CDCDB803 Registers

Table 8-4 lists the CDCDB803 registers. All register locations not listed in Table 8-4 should be considered as reserved locations and the register contents should not be modified.

Address	Acronym	Register Name	Section
0h	RCR1	Reserved Control Register 1	Go
1h	OECR1	Output Enable Control 1	Go
2h	OECR2	Output Enable Control 2	Go
3h	OERDBK	Output Enable# Pin Read Back	Go
4h	RCR2	Reserved Control Register 2	Go
5h	VDRREVID	Vendor/Revision Identification	Go
6h	DEVID	Device Identification	Go
7h	BTRDCNT	Byte Read Count Control	Go
8h	OUTSET	Output Setting Control	Go
4Ch	CAPTRIM	Slew Rate Capacitor Cluster 1 & 2	Go

Complex bit access types are encoded to fit into small table cells. Table 8-5 shows the codes that are used for access types in this section.

Access Type	Code	Description			
Read Type					
R	R	Read			
Write Type	Write Type				
W	W	Write			
Reset or Default	Reset or Default Value				
-n		Value after reset or the default value			

Table 8-5. CDCDB803 Access Type Codes

8.6.1.1 RCR1 Register (Address = 0h) [reset = 47h]

RCR1 is shown in Table 8-6.

Return to the Summary Table.

The RCR1 register contains reserved bits.

Table 8-6. RCR1	Register Field Descriptions
-----------------	------------------------------------

			- J -	
Bit	Field	Туре	Reset	Description
7-4	Reserved	R	4h	Reserved.
3-0	Reserved	R/W	7h	Writing to these bits will not affect the functionality of the device.

8.6.1.2 OECR1 Register (Address = 1h) [reset = FFh]

OECR1 is shown in OECR1 Register Field Descriptions.

Return to the Summary Table.

The OECR1 register contains bits that enable or disable individual output clock channels [5:0].



	Table 8-7. OECR1 Register Field Descriptions						
Bit	Field	Туре	Reset	Description			
7	OUT_EN_CLK5	R/W	1h	This bit controls the output enable signal for output channel CK5_P/ CK5_N. 0h = Output Disabled 1h = Output Enabled			
6	OUT_EN_CLK4	R/W	1h	This bit controls the output enable signal for output channel CK4_P/ CK4_N. 0h = Output Disabled 1h = Output Enabled			
5	OUT_EN_CLK3	R/W	1h	This bit controls the output enable signal for output channel CK3_P/ CK3_N. 0h = Output Disabled 1h = Output Enabled			
4	OUT_EN_CLK2	R/W	1h	This bit controls the output enable signal for output channel CK2_P/ CK2_N. 0h = Output Disabled 1h = Output Enabled			
3	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.			
2	OUT_EN_CLK1	R/W	1h	This bit controls the output enable signal for output channel CK1_P/ CK1_N. 0h = Output Disabled 1h = Output Enabled			
1	OUT_EN_CLK0	R/W	1h	This bit controls the output enable signal for output channel CK0_P/ CK0_N. 0h = Output Disabled 1h = Output Enabled			
0	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.			

Table 8-7. OECR1 Register Field Descriptions

8.6.1.3 OECR2 Register (Address = 2h) [reset = 0Fh]

OECR2 is shown in OECR2 Register Field Descriptions.

Return to the Summary Table.

The OECR2 register contains bits that enable or disable individual output clock channels [7:6].

	Table 6-6. DECK2 Register Field Descriptions									
Bit	Field	Туре	Reset	Description						
7-3	Reserved	R/W	1h	Writing to these bits will not affect the functionality of the device.						
2	OUT_EN_CLK7	R/W	1h	This bit controls the output enable signal for output channel CK7_P/ CK7_N. 0h = Output Disabled 1h = Output Enabled						
1	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.						
0	OUT_EN_CLK6	R/W	1h	This bit controls the output enable signal for output channel CK6_P/ CK6_N. Oh = Output Disabled 1h = Output Enabled						

Table 8-8. OECR2 Register Field Descriptions

8.6.1.4 OERDBK Register (Address = 3h) [reset = 0h]

OERDBK is shown in Table 8-9.

Return to the Summary Table.



The OERDBK register contains bits that report the current state of the OE[7:0]# input pins.

Tal	ble 8-9. O	ERDBK Reg	gister Field	Descriptions

Bit	Field	Туре	Reset	Description		
7	RB_OE7	R	0h	This bit reports the logic level present on the OE7# pin.		
6	RB_OE6	R	0h	This bit reports the logic level present on the OE6# pin.		
5	RB_OE5	R	0h	This bit reports the logic level present on the OE5# pin.		
4	RB_OE4	R	0h	This bit reports the logic level present on the OE4# pin.		
3	RB_OE3	R	0h	This bit reports the logic level present on the OE3# pin.		
2	RB_OE2	R	0h	This bit reports the logic level present on the OE2# pin.		
1	RB_OE1	R	0h	This bit reports the logic level present on the OE1# pin.		
0	RB_OE0	R	0h	This bit reports the logic level present on the OE0# pin.		

8.6.1.5 RCR2 Register (Address = 4h) [reset = 0h]

RCR2 is shown in RCR2 Register Field Descriptions.

Return to the Summary Table.

The RCR2 register contains reserved bits.

Table 8-10. RCR2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-0	Reserved	R	0h	Reserved.

8.6.1.6 VDRREVID Register (Address = 5h) [reset = 0Ah]

VDRREVID is shown in Table 8-11.

Return to the Summary Table.

The VDRREVID register contains a vendor identification code and silicon revision code.

Table 8-11. VDRREVID Register Field Descriptions								
Bit	Field	Туре	Reset	Description				
7-4	REV_ID	R	0h	Silicon revision code. Silicon revision code bits [3:0] map to register bits [7:4] directly.				
3-0	VENDOR_ID	R	Ah	Vendor identification code. Vendor ID bits [3:0] map to register bits [3:0] directly.				

8.6.1.7 DEVID Register (Address = 6h) [reset = E7h]

DEVID is shown in Table 8-12.

Return to the Summary Table.

The DEVID register contains a device identification code.

Bit	Field	Туре	Reset	Description
7-0	DEV_ID	R	E7h	Device ID code. Device ID bits[7:0] map to register bits[7:0] directly.



8.6.1.8 BTRDCNT Register (Address = 7h) [reset = 8h]

BTRDCNT is shown in Table 8-13.

Return to the Summary Table.

The BTRDCNT register contains bits [4:0] which configure the number of bytes which will be read back.

Bit	Field	Туре	Reset	Description					
7-5	Reserved	R/W	0h	Writing to these bits will not affect the functionality of the device.					
4	BYTE_COUNTER	R/W	0h	Writing to this register configures how many bytes will be read back.					
3-0	BYTE_COUNTER	R/W	8h	whiting to this register configures now many bytes will be read back.					

Table 8-13. BTRDCNT Register Field Descriptions

8.6.1.9 OUTSET Register (Address = 8h) [reset = 0h]

OUTSET is shown in Table 8-14.

Return to the Summary Table.

Bit5 of the OUTSET register sets the termination for all the outputs while bit4 can be used to set the power-down state for all outputs. The remaining bits for this register are reserved.

Bit	Field	Туре	Reset	Description
7-6	Reserved	R	Oh	Reserved.
5	CH_ZOUT_SEL	R/W	0h	Select between 85 Ω (0) and 100 Ω (1) Output impedance
4	d_DRIVE_OP_STATE_CTRL	R/W	Oh	Power-down state of all output clocks. 0: LOW/LOW 1: TRI_STATE
3-0	Reserved	R/W	0h	Register bits can be written to 0. Writing a different value than 0 will affect device functionality.

Table 8-14. OUTSET Register Field Descriptions

8.6.1.10 CAPTRIM Register (Address = 4Ch) [reset = 66h]

CAPTRIM is shown in Table 8-16.

Return to the Summary Table.

Bits [7:4] of the CAPTRIM register is used to control the slew rate for output channel cluster 2. Bits [3:0] control the slew rate for output channel cluster 1. Refer below for cluster identification.

Table 8-15. Cluster Identification Cluster Outputs

Cluster	Outputs
1	CK3, CK2, CK1, CK0
2	CK7, CK6, CK5, CK4

Table 8-16. CAPTRIM Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	CLUSTER2_CAP_TRIM	R/W	6h	Slew Rate Reduction Cap Trim for Cluster 2. Default value of 6h. 0: minimum F: maximum
3-0	CLUSTER1_CAP_TRIM	R/W	6h	Slew Rate Reduction Cap Trim for Cluster 1. Default value of 6h. 0: minimum F: maximum



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The CDCDB803 is a fanout buffer that supports PCIe generation 4 and PCIe generation 5 REFCLK distribution. The device is used to distribute up to eight copies of a typically 100-MHz clock.

9.2 Typical Application

Figure 9-1 shows a CDCDB803 typical application. In this application, a clock generator provides a 100-MHz reference to the CDCDB803 which then distributes that clock to PCIe endpoints. The clock generator may be a discrete clock generator like the CDCI6214 or it may be integrated in a larger component such as a Platform Controller Hub (PCH) or application processor.

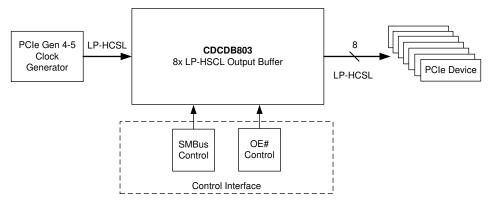


Figure 9-1. Typical Application

9.2.1 Design Requirements

Consider a typical server motherboard application which must distribute a 100-MHz PCIe reference clock from the PCH of a processor chipset to multiple endpoints. An example of clock input and output requirements is:

- Clock Input:
 - 100-MHz LP-HCSL
- Clock Output:
 - 2x 100-MHz to processors, LP-HCSL
 - 3x 100-MHz to riser/retimer, LP-HCSL
 - 3x 100-MHz to DDR memory controller, LP-HCSL



9.2.2 Detailed Design Procedure

The following items must be determined before starting design of a CDCDB803 socket:

- Output Enable Control Method
- SMBus address

9.2.2.1 Output Enable Control Method

The device provides an option to either use SMBus programmed registers (software) to control the outputs or by using the hardware OE# pins. In case of using software to control the outputs, the hardware OE# pins can be left floating as each of these pins have a pulldown to ground. Refer to Table 8-2 and the *Register Maps* section for more information on programming the register.

When the user wants to control the outputs with the hardware OE# pins, they can do so for example by connecting these pins to a GPIO controller and follow the *Pin Configuration and Functions* section to set the outputs to HIGH/LOW. The bits OUT_EN_CLK7 to OUT_EN_CLK0 used to control the outputs are shown in registers OECR1 (Table 8-7) and OECR2 (Table 8-8). These register bits are set to 1 by default to ensure that the outputs are "software enabled" and their state is therefore set by hardware OE# pins.

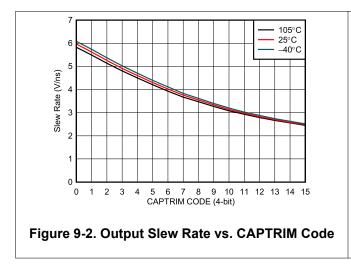
9.2.2.2 SMBus Address

An SMBus address should be selected from the listed potential addresses in Table 8-1. The appropriate pullup or pulldown resistor should be placed on the SADRx pins as indicated in the table. Ensure the SMBus address is not already in use to avoid conflict.

9.2.3 Application Curves

Figure 6-1 in the *Typical Characteristics* section can be used as both an application curve and a typical characteristics plot in this example.

The Figure 9-2 and Figure 9-3 show characterization data for the Output slew rate for various CAPTRIM codes and across temperature. Customers can use these plots as reference for choosing the appropriate output slew rate based on their system requirement.



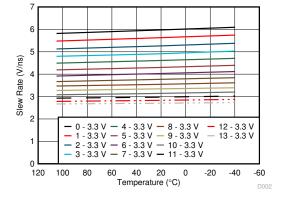


Figure 9-3. Slew Rate Variation Across Temperature for Different CAPTRIM Code



10 Power Supply Recommendations

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when the jitter and phase noise is critical to applications.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guards the power-supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly use the bypass capacitors, place the capacitors very close to the power-supply terminals and lay out with short loops to minimize inductance. TI recommends to insert a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer. These beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

Figure 10-1 shows the recommended power supply filtering and decoupling method.

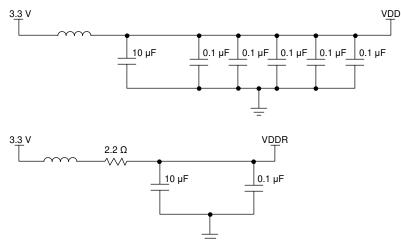


Figure 10-1. Power Supply Decoupling



11 Layout

11.1 Layout Guidelines

The following section provides the layout guidelines to ensure good thermal performance and power supply connections for the CDCDB803.

In *Layout Examples*, the CDCDB803 has $85-\Omega$ differential output impedance LP-HCSL format drivers as per register default settings. All transmission lines connected to CKx pins should be $85-\Omega$ differential impedance, $42.5-\Omega$ single-ended impedance to avoid reflections and increased radiated emissions. If $100-\Omega$ output impedance is enabled, the transmission lines connected to CKx pins should be $100-\Omega$ differential impedance, $50-\Omega$ single-ended impedance. Take care to eliminate or reduce stubs on the transmission lines.

11.2 Layout Examples

Figure 11-1 through Figure 11-3 are printed circuit board (PCB) layout examples that show the application of thermal design practices and a low-inductance ground connection between the device DAP and the PCB.

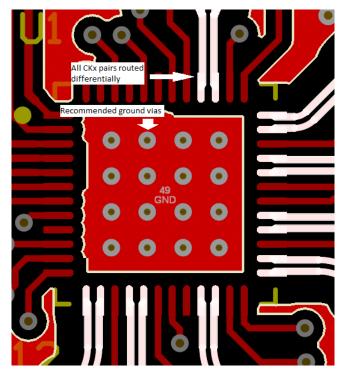


Figure 11-1. PCB Layout Example for CDCDB803, Top layer



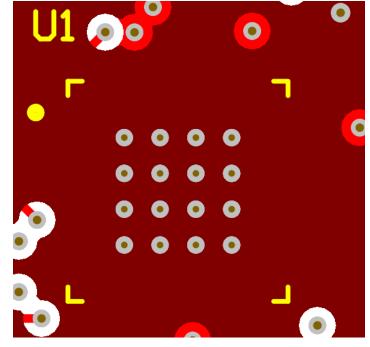


Figure 11-2. PCB Layout Example for CDCDB803, GND Layer

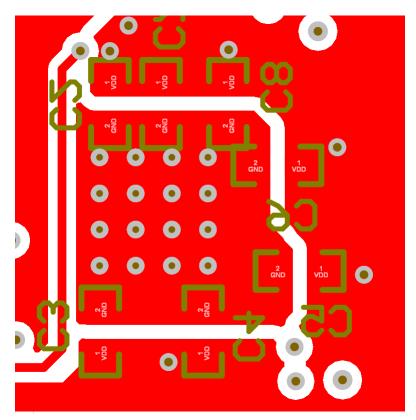


Figure 11-3. PCB Layout Example for CDCDB803, Bottom Layer



12 Device and Documentation Support

12.1 Device Support

12.1.1 TICS Pro

TICS Pro is an offline software tool for EVM programming and also for register map generation to program a device configuration for a specific application. For TICS Pro, go to https://www.ti.com/tool/TICSPRO-SW.

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments. All trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CDCDB803RSLR	ACTIVE	VQFN	RSL	48	4000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 105	CDCB803	Samples
CDCDB803RSLT	ACTIVE	VQFN	RSL	48	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 105	CDCB803	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



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PACKAGE OPTION ADDENDUM

4-May-2022

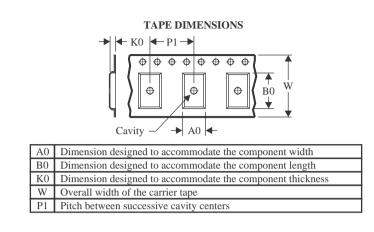


Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCDB803RSLR	VQFN	RSL	48	4000	330.0	16.4	6.3	6.3	1.1	12.0	16.0	Q2
CDCDB803RSLT	VQFN	RSL	48	250	180.0	16.4	6.3	6.3	1.1	12.0	16.0	Q2



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PACKAGE MATERIALS INFORMATION

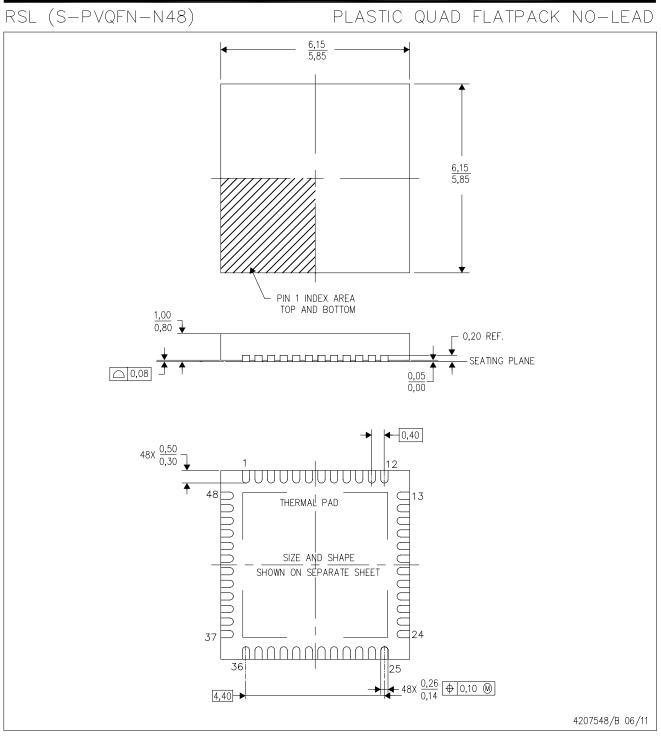
3-Jun-2022



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCDB803RSLR	VQFN	RSL	48	4000	367.0	367.0	35.0
CDCDB803RSLT	VQFN	RSL	48	250	210.0	185.0	35.0

MECHANICAL DATA



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Quad Flatpack, No-leads (QFN) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

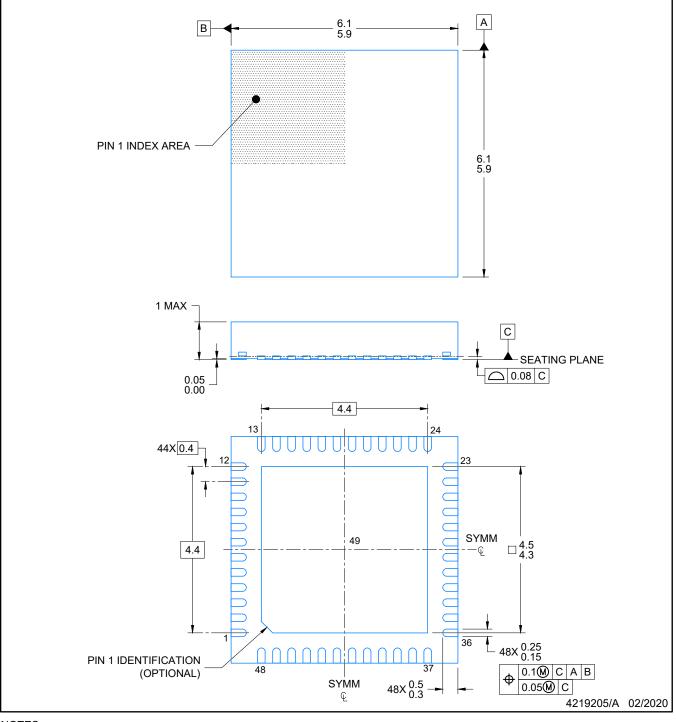


<u>RSL0048B</u>

PACKAGE OUTLINE

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

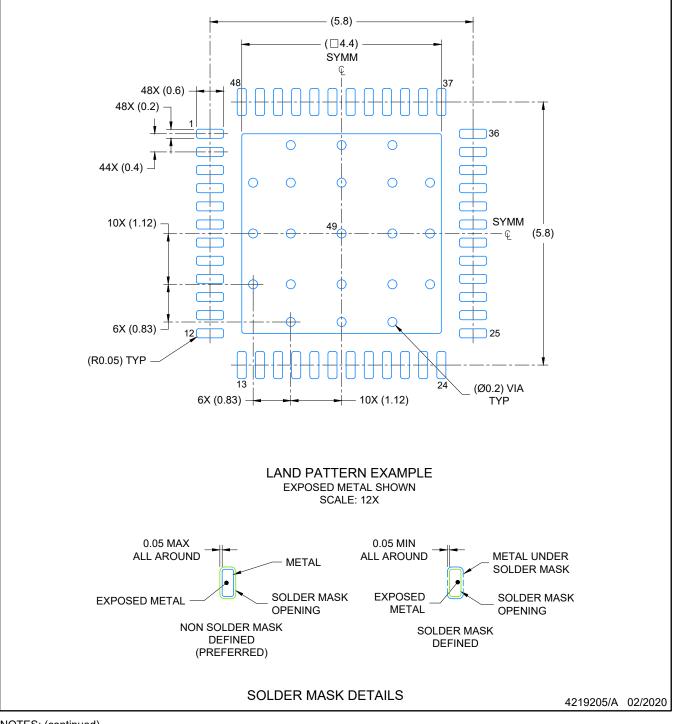


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EXAMPLE BOARD LAYOUT

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

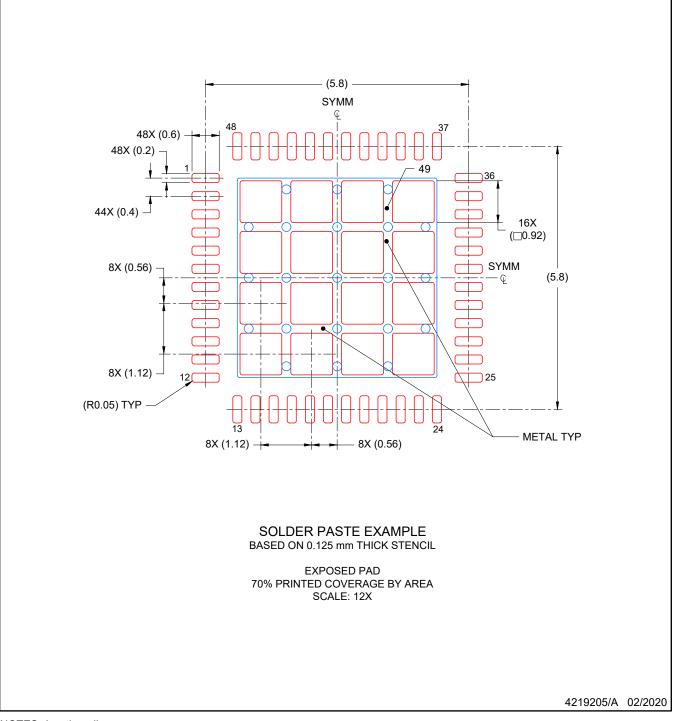


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EXAMPLE STENCIL DESIGN

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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